# 200 $\Omega$ , Low Leakage, Low Parasitic and Low Charge Injection, **Quad SPST Analog Switches**

#### **DESCRIPTION**

The DG2501, DG2502, and DG2503 are monolithic guad single-pole single-throw (SPST) analog switches that operate from a single 1.8 V to 5.5 V power supply.

These switches are fully specified at 3 V and 5 V. The parts feature low parasitic capacitance, low charge injection, and low leakage performance over the full operating temperature range of -40 °C to +85 °C. Their ESD/HBM tolerance is over 8 kV.

The DG2501, DG2502, and DG2503 each feature four independently selectable SPST switches with closely matched channel resistance. The DG2501 is normally closed, while the DG2502 is normally open.

The DG2503 has two normally open and two normally parts quaranteed closed switches. ΑII are break-before-make operation for use in multiplexer applications. The parts have a guaranteed control logic high of 1.4 V when V+ is 3 V and 1.8 V when V+ is 5 V.

Each switch conducts equally well in both directions when on, and each has an input signal range that extends to the supplies.

The DG2501, DG2502, and DG2503 are ideal for portable healthcare, instrument, and communication devices.

The DG2501, DG2502, and DG2503 are available in wafer level CSP package with top side lamination.

The package has a 4 x 4 bump array, 0.35 mm pitch, and 1.44 mm x 1.44 mm length and width.

#### **FEATURES**

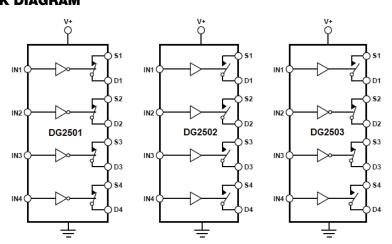
- 1.8 V to 5.5 V single supply operation
- Low leakage, 1 nA / max. at 85 °C
- · Low switch off capacitance
- Rail-to-rail signal handling
- Latch up current > 800 mA (JESD78)
- ESD: 8000 V/HBM
- Typical power consumption (< 0.01 μW)</li>
- TTL/CMOS compatible
- Compact WCSP16 1.44 mm x 1.44 mm
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



- Analog front end signal switching
- · Sample-and-hold circuits
- · Battery-powered systems
- Portable meters
- · Automatic test equipment
- · Medical and healthcare equipment
- Communication systems

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## **FUNCTIONAL BLOCK DIAGRAM**



Switches are shown for a Logic 0 Input

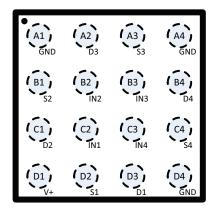
TRUTH TABLE									
DG2501 DG2502 DG2503									
LOGIC	SWITCH	LOGIC	SWITCH	LOGIC	SW1, SW4	SW2, SW3			
0	ON	0	OFF	0	OFF	ON			
1	OFF	1	ON	1	ON	OFF			

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ORDERING INFORMATION									
PART NUMBER	CONFIGURATION	SWITCH FUNCTION	TEMPERATURE RANGE	PACKAGE	REEL QUANTITY				
DG2501DB-T2-GE1	Quad SPST	NC	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000				
DG2501DB-T4-GE1	Quad SPST	NC	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000				
DG2502DB-T2-GE1	Quad SPST	NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000				
DG2502DB-T4-GE1	Quad SPST	NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000				
DG2503DB-T2-GE1	Quad SPST	NC/NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000				
DG2503DB-T4-GE1	Quad SPST	NC/NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000				

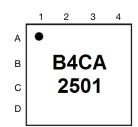
## **PACKAGE OUTLINE**



Top View (Bump Side Down)

Fig. 1 - Package Outline for WCSP16, 1.44 mm x 1.44 mm, 0.35 mm Pitch

## **DEVICE MARKING**



Row 1 Dot = Pin A1 Locator

Row 2 B = Fab, 4 = Year, C = Week Code, A = Lot Code

Row 3 2501 = Part Code

Fig. 2 - Device Marking

ABSOLUTE MAXIMUM RATINGS							
ELECTRICAL PARAMETERS	CONDITIONS	LIMITS	UNIT				
V+, INx	Reference to GND	-0.3 to +6	V				
Sx, Dx	Reference to GND	-0.3 to (V+) +0.3	]				
Maximum continuous switch current		5					
Maximum peak current (Pulsed 1 ms, 10 % duty cycle)		20	mA				
Thermal resistance		80	°C/W				
Latch up current	JESD78	> 800	mA				
ESD - HBM	ANSI / ESDA / JEDEC® JS-001	> 8000	V				
Temperature							
Operating temperature		-40 to +85	°C				
Storage temperature		-65 to +150					

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



		TEST CONDITION			-40 °C to +85 °C			
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED, V+ = 3 V	TEMP. b	TYP. c	MIN. d	MAX. d	UNIT	
		V <sub>INH</sub> = 1.4 V, V <sub>INL</sub> = 0.4 V <sup>a</sup>			WIIIN.	IVIAA.		
Analog Switch								
Analog signal range <sup>e</sup>	$V_{ANALOG}$		Full	1	0	3	V	
Drain-source on	B		Room	133	-	200		
resistance	R <sub>DS(on)</sub>	V <sub>S</sub> = 1.5 V, I <sub>S</sub> = -1 mA	Full	-	-	250	Ω	
On-resistance matching	$\Delta R_{on}$	V5 = 1.5 V, 15 = 1 1111	Room	0.83	-	10	22	
Off resistance matering	Zi ion		Full	=	-	13		
Switch off leakage current	I <sub>S</sub> /I <sub>D(off)</sub>	V+ = 3.3 V,	Room	± 0.016	-0.4	+0.4		
omion on loanage carrons	-3 -D(011)	$V_S = 0.3 \text{ V/3 V}, V_D = 3 \text{ V} / 0.3 \text{ V}$	Full	-	-1	+1	nA	
Channel on leakage	$I_{D(on)}$	V+ = 3.3 V,	Room	± 0.009	-0.4	+0.4		
current	·D(011)	V <sub>D</sub> = 0.3 V / 3 V	Full	-	-1	+1		
Digital Control			1		T	1		
Input, high voltage	$V_{INH}$		Full	-	1.4	-	V	
Input, low voltage	$V_{INL}$		Full	-	-	0.4	•	
Input leakage	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>GND</sub> or V+	Room	± 0.001	-	-	μΑ	
		VIN - VGND OI V+	Full	-	-0.1	+0.1		
Digital input capacitance e	$C_{IN}$	f = 1 MHz	Room	2	-	-	pF	
Dynamic Characteristics								
Break-before make time	t <sub>BBM</sub>	DG2503 only, $V_{S1} = V_{S2} = 1.5 \text{ V}$ ,	Room	47	10	-	ns	
Dieak-belole make time		$R_L = 300 \Omega C_L = 35 pF$	Full	-	10	-		
Turn-on time	t <sub>ON</sub>		Room	175	-	220		
Turn on time		$V_S = 1.5 \text{ V}, R_I = 300 \Omega, C_I = 35 \text{ pF}$	Full		-	250		
Turn-off time		ν <sub>3</sub> = 1.5 ν, τ.ξ = 555 ±2, σξ = 55 μ.	Room	77	-	100		
Turn on time			Full	-	-	120		
Charge injection e	$Q_{INJ}$	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 1.5 \text{ V}$	Room	-0.7	-	-	рС	
Off isolation e	OIRR	D = 50 0 C = 5 pF f = 1MHz	Room	-83	-	-	4D	
Cross talk e	X Talk	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1MHz$	Room	-85	-	-	dB	
3 dB bandwidth e	BW	$R_L = 50 \Omega$ , $C_L = 5 pF$	Room	510	-	-	MHz	
Source off capacitance e	C <sub>S(off)</sub>		Room	2.9	-	-		
Drain off capacitance e	C <sub>D(off)</sub>	f = 1 MHz, V <sub>S</sub> = 1.5 V	Room	2.8	-	-	pF	
Drain on capacitance e	•		Room	7.8	-	-		
Power Requirements	- (7		<u> </u>					
			Room	0.001	_	_		
Power supply current	l+	Digital input 0 or V+	Full		_	1	μΑ	



		TEST CONDITION	TEMP. b		-40 °C to +85 °C		
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED, V+ = 5 V		TYP. °	MIN. d	MAX. d	UNIT
		V <sub>INH</sub> = 1.8 V, V <sub>INL</sub> = 0.5 V <sup>a</sup>					
Analog Switch			T	T	T	,	
Analog signal range e	V <sub>ANALOG</sub>		Full	-	0	5	V
Drain-source on resistance	R <sub>DS(on)</sub>		Room	104	-	150	Ω
Brain ocaros orresistarios	03(011)	$V_S = 2.5 \text{ V}, I_S = -1 \text{ mA}$	Full	-	-	200	
On-resistance matching	$\Delta R_{on}$	23 2.0 1, 13 1.1.21	Room	0.39	-	8	
on reciciance matering			Full	-	-	10	
Switch off leakage current	I <sub>S</sub> /I <sub>D(off)</sub>	V+ = 5.5 V,	Room	± 0.022	-0.4	+0.4	
omion on roundgo ourronn	-3 -D(011)	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}$	Full	-	-1	+1	nA
Channel on leakage	I <sub>D(on)</sub>	V+ = 5.5 V,	Room	± 0.017	-0.4	+0.4	11/2
current	D(OII)	V <sub>D</sub> = 4.5 V/1 V	Full	-	-1	+1	
Digital Control			ı	ı	ı		
Input, high voltage	$V_{INH}$		Full	-	1.8	-	V
Input, low voltage	$V_{INL}$		Full	-	-	0.5	
Input leakage	I <sub>IN</sub>	$V_{IN} = V_{GND}$ or V+	Room	± 0.001	=	-	μΑ
mpuriounago		TIN TOND S. T.	Full	-	-1	+1	
Digital input capacitance e	C <sub>IN</sub>	f = 1 MHz	Room	2	-	-	рF
Dynamic Characteristics							
Break-before make time	t <sub>BBM</sub>	DG2503 only, $V_{S1} = V_{S2} = 3 V$ ,	Room	25	10	-	ns
Broak Boloro mako timo		$R_L = 300 \Omega C_L = 35 pF$	Full	-	10	-	
Turn-on time	t <sub>ON</sub>		Room	64	-	100	
		$V_S = 3 \text{ V}, R_I = 300 \Omega, C_I = 35 \text{ pF}$	Full	-	-	150	
Turn-off time	t <sub>OFF</sub>	13 2 1,112 222 25, 22 22 22	Room	38	-	60	
			Full	-	-	100	
Charge injection e	$Q_{INJ}$	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 3 \text{ V}$	Room	-2	-	-	рC
Off isolation e	OIRR	$R_1 = 50 \Omega$ , $C_1 = 5 pF$ , $f = 1MHz$	Room	-84	=	-	dB
Cross talk <sup>e</sup>	X Talk	11 = 30 sz, 0 = 3 pr , r = 111112	Room	-83	-	-	uБ
3 dB bandwidth <sup>e</sup>	BW	$R_L = 50 \Omega$ , $C_L = 5 pF$	Room	550	-	-	MHz
Source off capacitance e	C <sub>S(off)</sub>		Room	2.7	-	-	
Drain off capacitance e	C <sub>D(off)</sub>	f = 1 MHz, V <sub>S</sub> = 3 V	Room	2.6	-	-	рF
Drain on capacitance e	C <sub>D(on)</sub>		Room	7.6	_	-	•
Power Requirements	()		<u> </u>		l	<u> </u>	
		Digital input = 1.8 V, at one channel	Room	4.6	_	_	
		V+=5 V	Full	-	-	30	_
Power supply current	l+		Room	0.001	-	-	- μA
		Digital input 0 or V+	Full	_	_	2	

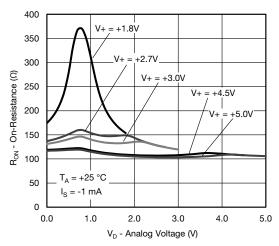
### Notes

- a. V<sub>IN</sub> = input voltage to perform proper function
- b. Room = 25 °C, Full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. The convention where the most negative value is a minimum and the most positive a maximum, is used in this data sheet
- e. Guaranteed by design, not subject to production test

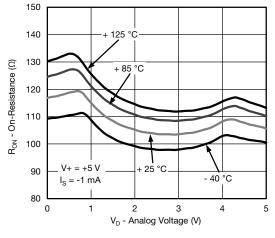
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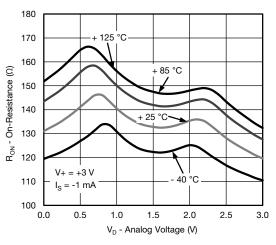
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



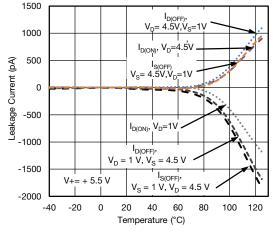
On-Resistance vs. Analog Voltage



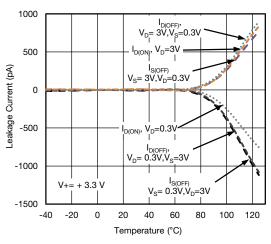
On-Resistance vs. Analog Voltage



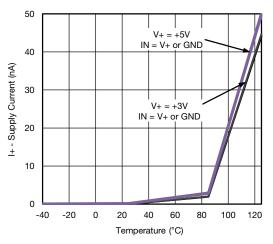
On-Resistance vs. Analog Voltage



Leakage Current vs. Temperature

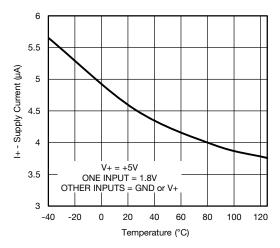


Leakage Current vs. Temperature

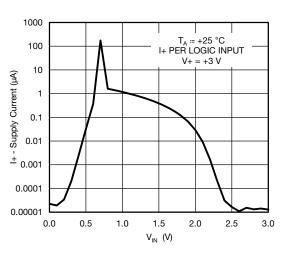


Supply Current vs. Temperature

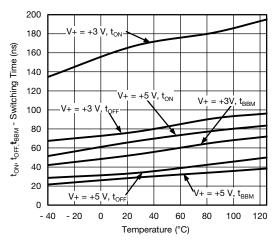
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



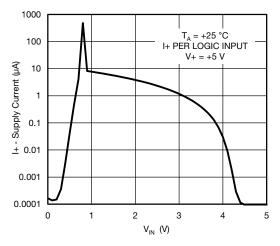
Supply Current vs. Temperature



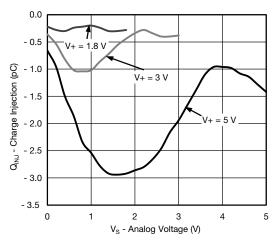
Supply Current vs. VIN



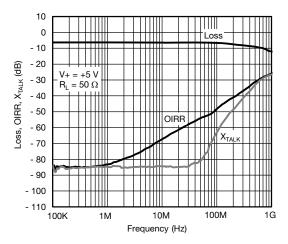
Switching Time vs. Temperature



Supply Current vs. VIN

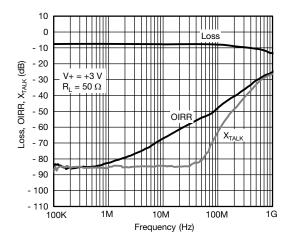


Charge Injection vs. Analog Voltage

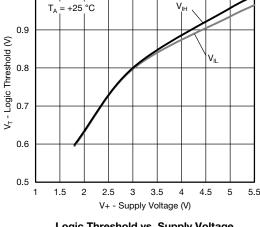


Loss, OIRR, X<sub>TALK</sub> vs. Frequency

## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

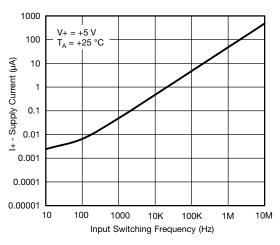


Loss, OIRR, X<sub>TALK</sub> vs. Frequency

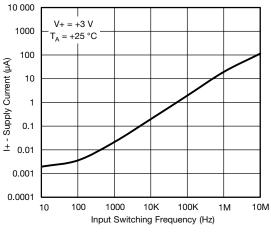


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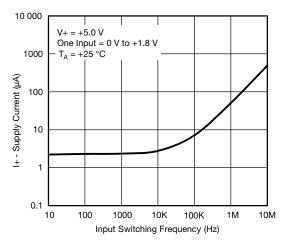
Logic Threshold vs. Supply Voltage



**Supply Current vs. Input Switching Frequency** 

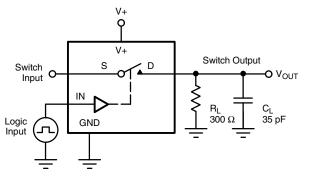


**Supply Current vs. Input Switching Frequency** 



**Supply Current vs. Input Switching Frequency** 

## **TEST CIRCUIT**



 $t_r < 5 \text{ ns}$ < 5 ns  $V_{INL}$ 0.9 x V<sub>OUT</sub> 0 V toN

 $V_{\text{INH}}$ 

Logic

Input

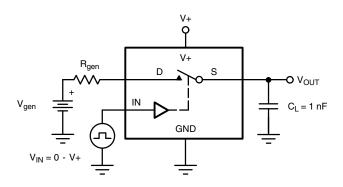
Switch Output

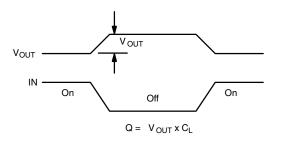
C<sub>L</sub> (includes fixture and stray capacitance)

$$V_{OUT} = V_{D} \left( \frac{R_{L}}{R_{L} + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

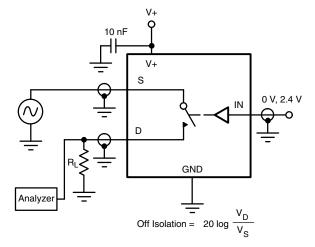
#### Fig. 3 - Switching Time





IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 4 - Charge Injection



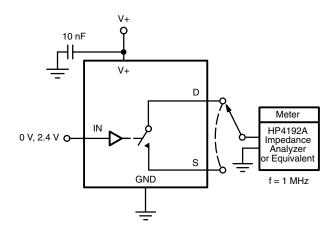


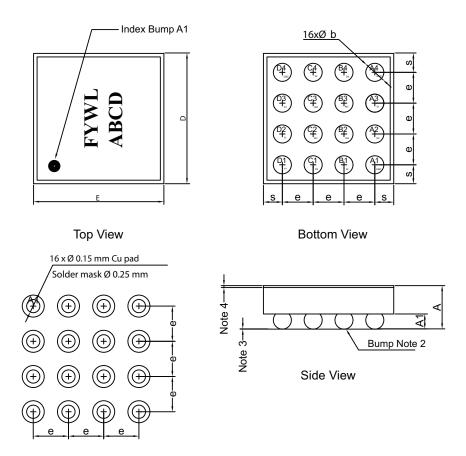
Fig. 5 - Off-Isolation

Fig. 6 - Channel Off/On Capacitance

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# **WCSP 4 x 4: 16 Bumps**

(4 x 4, 0.35 mm pitch, 172 μm bump height, 1.48 mm x 1.48 mm die size)



Recommended Land Pattern (NSMD)

# DWG: 6022

#### Notes

- (1) Laser mark on the silicon die back, coated with an epoxy film
- (2) Bumps are SAC405
- (3) 0.05 max. co-planarity
- (4) Laminate tape thickness is 0.022 mm

DIM.	MILLIMETERS a			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.444	0.474	0.504	0.0175	0.0187	0.0198	
A1	0.146	0.172	0.198	0.0057	0.0068	0.0078	
b	0.165	0.205	0.245	0.0065	0.0081	0.0096	
е	0.350				0.0138		
S	0.175	0.195	0.215	0.0069	0.0077	0.0085	
D	1.400	1.440	1.480	0.0551	0.0567	0.0583	
Е	1.400	1.440	1.480	0.0551	0.0567	0.0583	

## Note

a. Use millimeters as the primary measurement.



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PI5A4157ZUEX PI5A3166TAEX FSA634UCX TC4066BP(N,F) DG302BDJ-E3 PI5A100QEX HV2605FG-G HV2301FG-G

RS2117YUTQK10 RS2118YUTQK10 RS2227XUTQK10 ADG452BRZ-REEL7 MAX4066ESD+ MAX391CPE+ MAX4730EXT+T

MAX314CPE+ BU4066BCFV-E2 MAX313CPE+ BU4S66G2-TR NLASB3157MTR2G TS3A4751PWR NLAST4599DFT2G

NLAST4599DTT1G DG300BDJ-E3 DG2503DB-T2-GE1 TC4W53FU(TE12L,F) 74HC2G66DC.125 ADG619BRMZ-REEL DG2535EDQ
T1-GE3 LTC201ACN#PBF 74LV4066DB,118 FSA2275AUMX DIO1500WL12 ADG742BKSZ-REEL7 DIO1269LP10